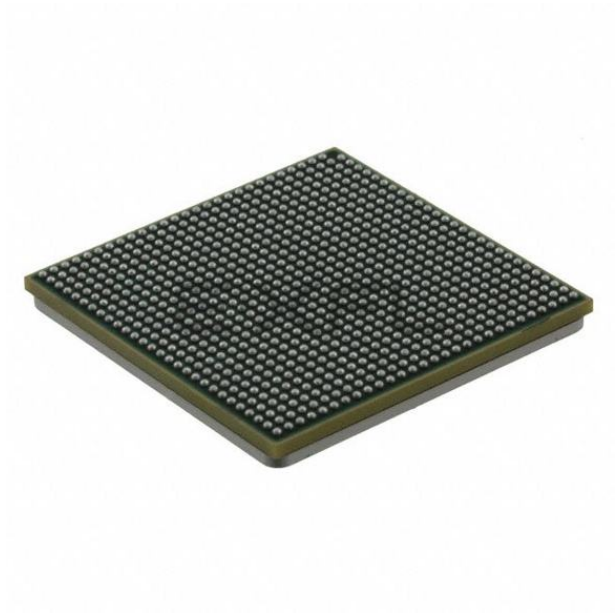

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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e500
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	533MHz
Co-Processors/DSP	-
RAM Controllers	DDR, SDRAM
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	-
USB	-
Voltage - I/O	2.5V, 3.3V
Operating Temperature	-40°C ~ 105°C (TA)
Security Features	-
Package / Case	1023-BFBGA, FCBGA
Supplier Device Package	1023-FCBGA (33x33)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mpc8541cvtajd

1 Overview

The following section provides a high-level overview of the MPC8541E features. Figure 1 shows the major functional units within the MPC8541E.

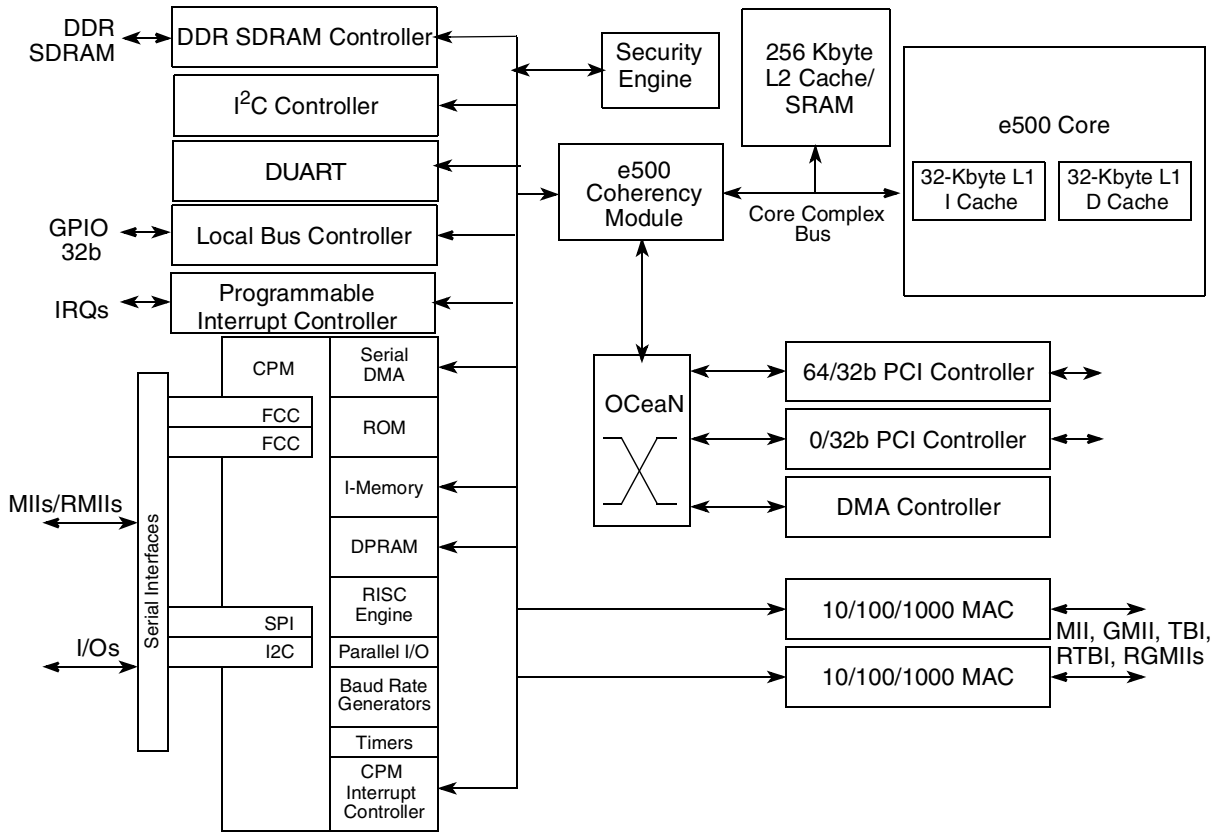


Figure 1. MPC8541E Block Diagram

1.1 Key Features

The following lists an overview of the MPC8541E feature set.

- Embedded e500 Book E-compatible core
  - High-performance, 32-bit Book E-enhanced core that implements the PowerPC architecture
  - Dual-issue superscalar, 7-stage pipeline design
  - 32-Kbyte L1 instruction cache and 32-Kbyte L1 data cache with parity protection
  - Lockable L1 caches—entire cache or on a per-line basis
  - Separate locking for instructions and data
  - Single-precision floating-point operations
  - Memory management unit especially designed for embedded applications
  - Enhanced hardware and software debug support
  - Dynamic power management
  - Performance monitor facility

  - 1000 Mbps IEEE 802.3z TBI
  - 10/100/1000 Mbps RGMII/RTBI
- Full- and half-duplex support
- Buffer descriptors are backwards compatible with MPC8260 and MPC860T 10/100 programming models
- 9.6-Kbyte jumbo frame support
- RMON statistics support
- 2-Kbyte internal transmit and receive FIFOs
- MII management interface for control and status
- Programmable CRC generation and checking

- OCeaN switch fabric
  - Three-port crossbar packet switch
  - Reorders packets from a source based on priorities
  - Reorders packets to bypass blocked packets
  - Implements starvation avoidance algorithms
  - Supports packets with payloads of up to 256 bytes
- Integrated DMA controller
  - Four-channel controller
  - All channels accessible by both local and remote masters
  - Extended DMA functions (advanced chaining and striding capability)
  - Support for scatter and gather transfers
  - Misaligned transfer capability
  - Interrupt on completed segment, link, list, and error
  - Supports transfers to or from any local memory or I/O port
  - Selectable hardware-enforced coherency (snoop/no-snoop)
  - Ability to start and flow control each DMA channel from external 3-pin interface
  - Ability to launch DMA from single write transaction
- PCI Controllers
  - PCI 2.2 compatible
  - One 64-bit or two 32-bit PCI ports supported at 16 to 66 MHz
  - Host and agent mode support, 64-bit PCI port can be host or agent, if two 32-bit ports, only one can be an agent
  - 64-bit dual address cycle (DAC) support
  - Supports PCI-to-memory and memory-to-PCI streaming
  - Memory prefetching of PCI read accesses
  - Supports posting of processor-to-PCI and PCI-to-memory writes
  - PCI 3.3-V compatible

  - Selectable hardware-enforced coherency
  - Selectable clock source (SYSCLK or independent PCI_CLK)
- Power management
  - Fully static 1.2-V CMOS design with 3.3- and 2.5-V I/O
  - Supports power save modes: doze, nap, and sleep
  - Employs dynamic power management
  - Selectable clock source (sysclk or independent PCI_CLK)
- System performance monitor
  - Supports eight 32-bit counters that count the occurrence of selected events
  - Ability to count up to 512 counter specific events
  - Supports 64 reference events that can be counted on any of the 8 counters
  - Supports duration and quantity threshold counting
  - Burstiness feature that permits counting of burst events with a programmable time between bursts
  - Triggering and chaining capability
  - Ability to generate an interrupt on overflow
- System access port
  - Uses JTAG interface and a TAP controller to access entire system memory map
  - Supports 32-bit accesses to configuration registers
  - Supports cache-line burst accesses to main memory
  - Supports large block (4-Kbyte) uploads and downloads
  - Supports continuous bit streaming of entire block for fast upload and download
- IEEE Std 1149.1™-compatible, JTAG boundary scan
- 783 FC-PBGA package

2 Electrical Characteristics

This section provides the AC and DC electrical specifications and thermal characteristics for the MPC8541E. The MPC8541E is currently targeted to these specifications. Some of these specifications are independent of the I/O cell, but are included for a more complete reference. These are not purely I/O buffer design specifications.

2.1 Overall DC Electrical Characteristics

This section covers the ratings, conditions, and other characteristics.

2.1.1 Absolute Maximum Ratings

Table 1 provides the absolute maximum ratings.

Table 1. Absolute Maximum Ratings [1]

Characteristic		Symbol	Max Value	Unit	Notes
Core supply voltage		V_{DD}	–0.3 to 1.32 0.3 to 1.43 (for 1 GHz only)	V	
PLL supply voltage		AV_{DD}	–0.3 to 1.32 0.3 to 1.43 (for 1 GHz only)	V	
DDR DRAM I/O voltage		GV_{DD}	–0.3 to 3.63	V	
Three-speed Ethernet I/O, MII management voltage		LV_{DD}	–0.3 to 3.63 –0.3 to 2.75	V	
CPM, PCI, local bus, DUART, system control and power management, I^2C, and JTAG I/O voltage		OV_{DD}	–0.3 to 3.63	V	3
Input voltage	DDR DRAM signals	MV_{IN}	–0.3 to (GV_{DD} + 0.3)	V	2, 5
	DDR DRAM reference	MV_{REF}	–0.3 to (GV_{DD} + 0.3)	V	2, 5
	Three-speed Ethernet signals	LV_{IN}	–0.3 to (LV_{DD} + 0.3)	V	4, 5
	CPM, Local bus, DUART, SYSCLK, system control and power management, I^2C, and JTAG signals	OV_{IN}	–0.3 to (OV_{DD} + 0.3)1	V	5
	PCI	OV_{IN}	–0.3 to (OV_{DD} + 0.3)	V	6
Storage temperature range		T_{STG}	–55 to 150	°C	

Notes:
1. Functional and tested operating conditions are given in Table 2. Absolute maximum ratings are stress ratings only, and functional operation at the maximums is not guaranteed. Stresses beyond those listed may affect device reliability or cause permanent damage to the device.
2. **Caution:** MV_{IN} must not exceed GV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
3. **Caution:** OV_{IN} must not exceed OV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
4. **Caution:** LV_{IN} must not exceed LV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
5. (M,L,O)V_{IN} and MV_{REF} may overshoot/undershoot to a voltage and for a maximum duration as shown in Figure 2.
6. OV_{IN} on the PCI interface may overshoot/undershoot according to the PCI Electrical Specification for 3.3-V operation, as shown in Figure 3.

2.1.2 Power Sequencing

The MPC8541Erequires its power rails to be applied in a specific sequence in order to ensure proper device operation. These requirements are as follows for power up:

1. V_{DD}, AV_{DDn}
2. GV_{DD}, LV_{DD}, OV_{DD} (I/O supplies)

Items on the same line have no ordering requirement with respect to one another. Items on separate lines must be ordered sequentially such that voltage rails on a previous step must reach 90 percent of their value before the voltage rails on the current step reach ten percent of theirs.

NOTE

If the items on line 2 must precede items on line 1, please ensure that the delay does not exceed 500 ms and the power sequence is not done greater than once per day in production environment.

NOTE

From a system standpoint, if the I/O power supplies ramp prior to the V_{DD} core supply, the I/Os on the MPC8541E may drive a logic one or zero during power-up.

2.1.3 Recommended Operating Conditions

Table 2 provides the recommended operating conditions for the MPC8541E. Note that the values in Table 2 are the recommended and tested operating conditions. Proper device operation outside of these conditions is not guaranteed.

Table 2. Recommended Operating Conditions

Characteristic		Symbol	Recommended Value	Unit
Core supply voltage		V_{DD}	1.2 V ± 60 mV 1.3 V± 50 mV (for 1 GHz only)	V
PLL supply voltage		AV_{DD}	1.2 V ± 60 mV 1.3 V ± 50 mV (for 1 GHz only)	V
DDR DRAM I/O voltage		GV_{DD}	2.5 V ± 125 mV	V
Three-speed Ethernet I/O voltage		LV_{DD}	3.3 V ± 165 mV 2.5 V ± 125 mV	V
PCI, local bus, DUART, system control and power management, I^2C, and JTAG I/O voltage		OV_{DD}	3.3 V ± 165 mV	V
Input voltage	DDR DRAM signals	MV_{IN}	GND to GV_{DD}	V
	DDR DRAM reference	MV_{REF}	GND to GV_{DD}	V
	Three-speed Ethernet signals	LV_{IN}	GND to LV_{DD}	V
	PCI, local bus, DUART, SYSCLK, system control and power management, I^2C, and JTAG signals	OV_{IN}	GND to OV_{DD}	V
Die-junction Temperature		T_j	0 to 105	°C

Figure 3 shows the undershoot and overshoot voltage of the PCI interface of the MPC8541E for the 3.3-V signals, respectively.

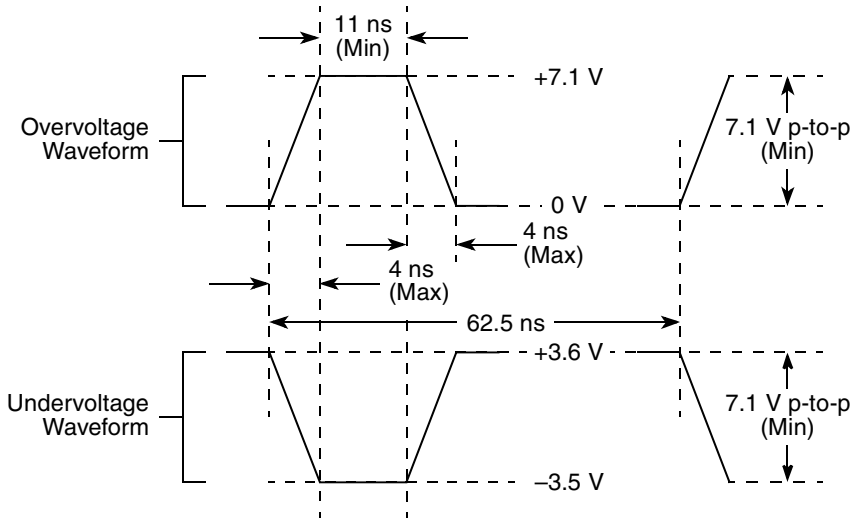


Figure 3. Maximum AC Waveforms on PCI interface for 3.3-V Signaling

2.1.4 Output Driver Characteristics

Table 3 provides information on the characteristics of the output driver strengths. The values are preliminary estimates.

Table 3. Output Drive Capability

Driver Type	Programmable Output Impedance (Ω)	Supply Voltage	Notes
Local bus interface utilities signals	25	OV_{DD} = 3.3 V	1
	42 (default)		
PCI signals	25		2
	42 (default)		
DDR signal	20	GV_{DD} = 2.5 V	
TSEC/10/100 signals	42	LV_{DD} = 2.5/3.3 V	
DUART, system control, I2C, JTAG	42	OV_{DD} = 3.3 V	

Notes:
1. The drive strength of the local bus interface is determined by the configuration of the appropriate bits in PORIMPSCR.
2. The drive strength of the PCI interface is determined by the setting of the $\overline{\text{PCI\_GNT1}}$ signal at reset.

6.2 DDR SDRAM AC Electrical Characteristics

This section provides the AC electrical characteristics for the DDR SDRAM interface.

6.2.1 DDR SDRAM Input AC Timing Specifications

Table 13 provides the input AC timing specifications for the DDR SDRAM interface.

Table 13. DDR SDRAM Input AC Timing Specifications

At recommended operating conditions with GV_{DD} of 2.5 V ± 5%.

Parameter	Symbol	Min	Max	Unit	Notes
AC input low voltage	V_{IL}	—	MV_{REF} – 0.31	V	—
AC input high voltage	V_{IH}	MV_{REF} + 0.31	GV_{DD} + 0.3	V	—
MDQS—MDQ/MECC input skew per byte For DDR = 333 MHz For DDR ≤ 266 MHz	t_{DISKEW}	—	 750 1125	ps	1

Note:

1. Maximum possible skew between a data strobe (MDQS[n]) and any corresponding bit of data (MDQ[8n + {0...7}] if 0 <= n <= 7) or ECC (MECC[{0...7}] if n = 8).

6.2.2 DDR SDRAM Output AC Timing Specifications

Table 14 and Table 15 provide the output AC timing specifications and measurement conditions for the DDR SDRAM interface.

Table 14. DDR SDRAM Output AC Timing Specifications for Source Synchronous Mode

At recommended operating conditions with GV_{DD} of 2.5 V ± 5%.

Parameter	Symbol [1]	Min	Max	Unit	Notes
MCK[n] cycle time, (MCK[n]/$\overline{\text{MCK}}$[n] crossing)	t_{MCK}	6	10	ns	2
Skew between any MCK to ADDR/CMD 333 MHz 266 MHz 200 MHz	t_{AOSKEW}	 –1000 –1100 –1200	 200 300 400	ps	3
ADDR/CMD output setup with respect to MCK 333 MHz 266 MHz 200 MHz	t_{DDKHAS}	 2.8 3.45 4.6	—	ns	4
ADDR/CMD output hold with respect to MCK 333 MHz 266 MHz 200 MHz	t_{DDKHAX}	 2.0 2.65 3.8	—	ns	4
$\overline{\text{MCS}}$(n) output setup with respect to MCK 333 MHz 266 MHz 200 MHz	t_{DDKHCS}	 2.8 3.45 4.6	—	ns	4

Figure 15 shows the MII management AC timing diagram.

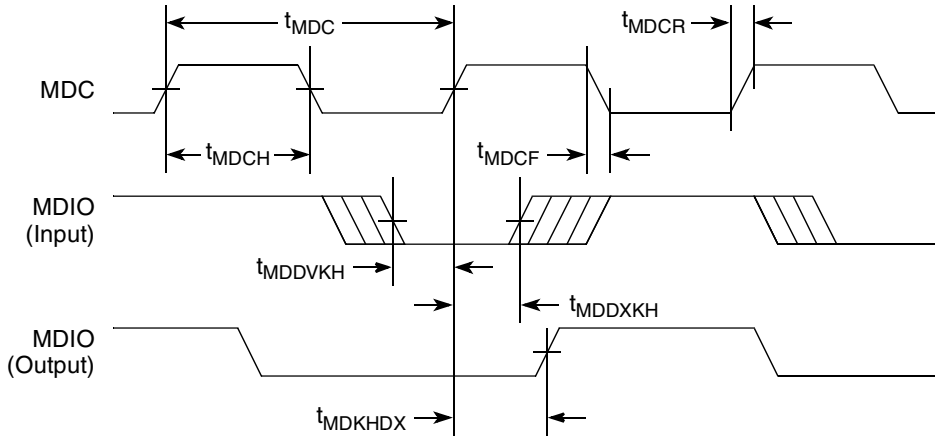


Figure 15. MII Management Interface Timing Diagram

9 Local Bus

This section describes the DC and AC electrical specifications for the local bus interface of the MPC8541E.

9.1 Local Bus DC Electrical Characteristics

Table 29 provides the DC electrical characteristics for the local bus interface.

Table 29. Local Bus DC Electrical Characteristics

Parameter	Symbol	Test Condition	Min	Max	Unit
High-level input voltage	V_{IH}	$V_{OUT} \geq V_{OH}$ (min) or	2	OV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	$V_{OUT} \leq V_{OL}$ (max)	–0.3	0.8	V
Input current	I_{IN}	V_{IN} [1] = 0 V or $V_{IN} = V_{DD}$	—	±5	μA
High-level output voltage	V_{OH}	OV_{DD} = min, I_{OH} = –2mA	OV_{DD} –0.2	—	V
Low-level output voltage	V_{OL}	OV_{DD} = min, I_{OL} = 2mA	—	0.2	V

Note:
1. Note that the symbol V_{IN}, in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

9.2 Local Bus AC Electrical Specifications

Table 30 describes the general timing parameters of the local bus interface of the MPC8541E with the DLL enabled.

Table 30. Local Bus General Timing Parameters—DLL Enabled

Parameter	Configuration [7]	Symbol [1]	Min	Max	Unit	Notes
Local bus cycle time		t_{LBK}	6.0	—	ns	2
LCLK[n] skew to LCLK[m] or LSYNC_OUT		$t_{LBKSKEW}$	—	150	ps	7, 9
Input setup to local bus clock (except LUPWAIT)		$t_{LBIVKH1}$	1.8	—	ns	3, 4, 8
LUPWAIT input setup to local bus clock		$t_{LBIVKH2}$	1.7	—	ns	3, 4
Input hold from local bus clock (except LUPWAIT)		$t_{LBIXKH1}$	0.5	—	ns	3, 4, 8
LUPWAIT input hold from local bus clock		$t_{LBIXKH2}$	1.0	—	ns	3, 4
LALE output transition to LAD/LDP output transition (LATCH hold time)		t_{LBOTOT}	1.5	—	ns	6
Local bus clock to output valid (except LAD/LDP and LALE)	$\overline{LWE[0:1]}$ = 00	$t_{LBKHOV1}$	—	2.3	ns	3, 8
	$\overline{LWE[0:1]}$ = 11 (default)			3.8		
Local bus clock to data valid for LAD/LDP	$\overline{LWE[0:1]}$ = 00	$t_{LBKHOV2}$	—	2.5	ns	3, 8
	$\overline{LWE[0:1]}$ = 11 (default)			4.0		
Local bus clock to address valid for LAD	$\overline{LWE[0:1]}$ = 00	$t_{LBKHOV3}$	—	2.6	ns	3, 8
	$\overline{LWE[0:1]}$ = 11 (default)			4.1		
Output hold from local bus clock (except LAD/LDP and LALE)	$\overline{LWE[0:1]}$ = 00	$t_{LBKHOX1}$	0.7	—	ns	3, 8
	$\overline{LWE[0:1]}$ = 11 (default)		1.6			
Output hold from local bus clock for LAD/LDP	$\overline{LWE[0:1]}$ = 00	$t_{LBKHOX2}$	0.7	—	ns	3, 8
	$\overline{LWE[0:1]}$ = 11 (default)		1.6			
Local bus clock to output high Impedance (except LAD/LDP and LALE)	$\overline{LWE[0:1]}$ = 00	$t_{LBKHOZ1}$	—	2.8	ns	5, 9
	$\overline{LWE[0:1]}$ = 11 (default)			4.2		

Table 30. Local Bus General Timing Parameters—DLL Enabled (continued)

Parameter	Configuration [7]	Symbol [1]	Min	Max	Unit	Notes
Local bus clock to output high impedance for LAD/LDP	$\overline{\text{LWE}}[0:1]$ = 00	$t_{LBKHOZ2}$	—	2.8	ns	5, 9
	$\overline{\text{LWE}}[0:1]$ = 11 (default)			4.2		

Notes:
1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(First two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(First two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one(1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to LSYNC_IN for DLL enabled mode.
3. All signals are measured from $OV_{DD}/2$ of the rising edge of LSYNC_IN for DLL enabled to $0.4 \times OV_{DD}$ of the signal in question for 3.3-V signaling levels.
4. Input timings are measured at the pin.
5. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
6. The value of t_{LBOTOT} is defined as the sum of 1/2 or 1 ccb_clk cycle as programmed by LBCR[AHD], and the number of local bus buffer delays used as programmed at power-on reset with configuration pins $\overline{\text{LWE}}[0:1]$.
7. Maximum possible clock skew between a clock LCLK[m] and a relative clock LCLK[n]. Skew measured between complementary signals at $OV_{DD}/2$.
8. Guaranteed by characterization.
9. Guaranteed by design.

Table 31 describes the general timing parameters of the local bus interface of the MPC8541E with the DLL bypassed.

Table 31. Local Bus General Timing Parameters—DLL Bypassed

Parameter	Configuration [7]	Symbol [1]	Min	Max	Unit	Notes
Local bus cycle time	—	t_{LBK}	6.0	—	ns	2
Internal launch/capture clock to LCLK delay	—	t_{LBKHKT}	1.8	3.4	ns	8
LCLK[n] skew to LCLK[m] or LSYNC_OUT	—	$t_{LBKSKEW}$	—	150	ps	7, 9
Input setup to local bus clock (except LUPWAIT)	—	$t_{LBIVKH1}$	5.2	—	ns	3, 4
LUPWAIT input setup to local bus clock	—	$t_{LBIVKH2}$	5.1	—	ns	3, 4
Input hold from local bus clock (except LUPWAIT)	—	$t_{LBIXKH1}$	–1.3	—	ns	3, 4
LUPWAIT input hold from local bus clock	—	$t_{LBIXKH2}$	–0.8	—	ns	3, 4
LALE output transition to LAD/LDP output transition (LATCH hold time)	—	t_{LBOTOT}	1.5	—	ns	6
Local bus clock to output valid (except LAD/LDP and LALE)	$\overline{\text{LWE}}[0:1]$ = 00	$t_{LBKLOV1}$	—	0.5	ns	3
	$\overline{\text{LWE}}[0:1]$ = 11 (default)			2.0		
Local bus clock to data valid for LAD/LDP	$\overline{\text{LWE}}[0:1]$ = 00	$t_{LBKLOV2}$	—	0.7	ns	3
	$\overline{\text{LWE}}[0:1]$ = 11 (default)			2.2		

Table 31. Local Bus General Timing Parameters—DLL Bypassed (continued)

Parameter	Configuration [7]	Symbol [1]	Min	Max	Unit	Notes
Local bus clock to address valid for LAD	$\overline{\text{LWE}}[0:1]$ = 00	$t_{LBKLOV3}$	—	0.8	ns	3
	$\overline{\text{LWE}}[0:1]$ = 11 (default)			2.3		
Output hold from local bus clock (except LAD/LDP and LALE)	$\overline{\text{LWE}}[0:1]$ = 00	$t_{LBKLOX1}$	–2.7	—	ns	3
	$\overline{\text{LWE}}[0:1]$ = 11 (default)		–1.8			
Output hold from local bus clock for LAD/LDP	$\overline{\text{LWE}}[0:1]$ = 00	$t_{LBKLOX2}$	–2.7	—	ns	3
	$\overline{\text{LWE}}[0:1]$ = 11 (default)		–1.8			
Local bus clock to output high Impedance (except LAD/LDP and LALE)	$\overline{\text{LWE}}[0:1]$ = 00	$t_{LBKLOZ1}$	—	1.0	ns	5
	$\overline{\text{LWE}}[0:1]$ = 11 (default)			2.4		
Local bus clock to output high impedance for LAD/LDP	$\overline{\text{LWE}}[0:1]$ = 00	$t_{LBKLOZ2}$	—	1.0	ns	5
	$\overline{\text{LWE}}[0:1]$ = 11 (default)			2.4		

Notes:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(First two letters of functional block)(signal)(state) (reference)(state)}}$ for inputs and $t_{\text{(First two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one(1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to LSYNC_IN for DLL enabled mode.
3. All signals are measured from $OV_{DD}/2$ of the rising edge of local bus clock for DLL bypass mode to $0.4 \times OV_{DD}$ of the signal in question for 3.3-V signaling levels.
4. Input timings are measured at the pin.
5. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
6. The value of t_{LBOTOT} is defined as the sum of 1/2 or 1 ccb_clk cycle as programmed by LBCR[AHD], and the number of local bus buffer delays used as programmed at power-on reset with configuration pins $\overline{\text{LWE}}[0:1]$.
7. Maximum possible clock skew between a clock LCLK[m] and a relative clock LCLK[n]. Skew measured between complementary signals at $OV_{DD}/2$.
8. Guaranteed by characterization.
9. Guaranteed by design.

Figure 16 provides the AC test load for the local bus.

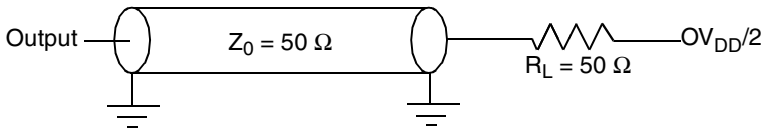


Figure 16. Local Bus C Test Load

Figure 17 to Figure 22 show the local bus signals.

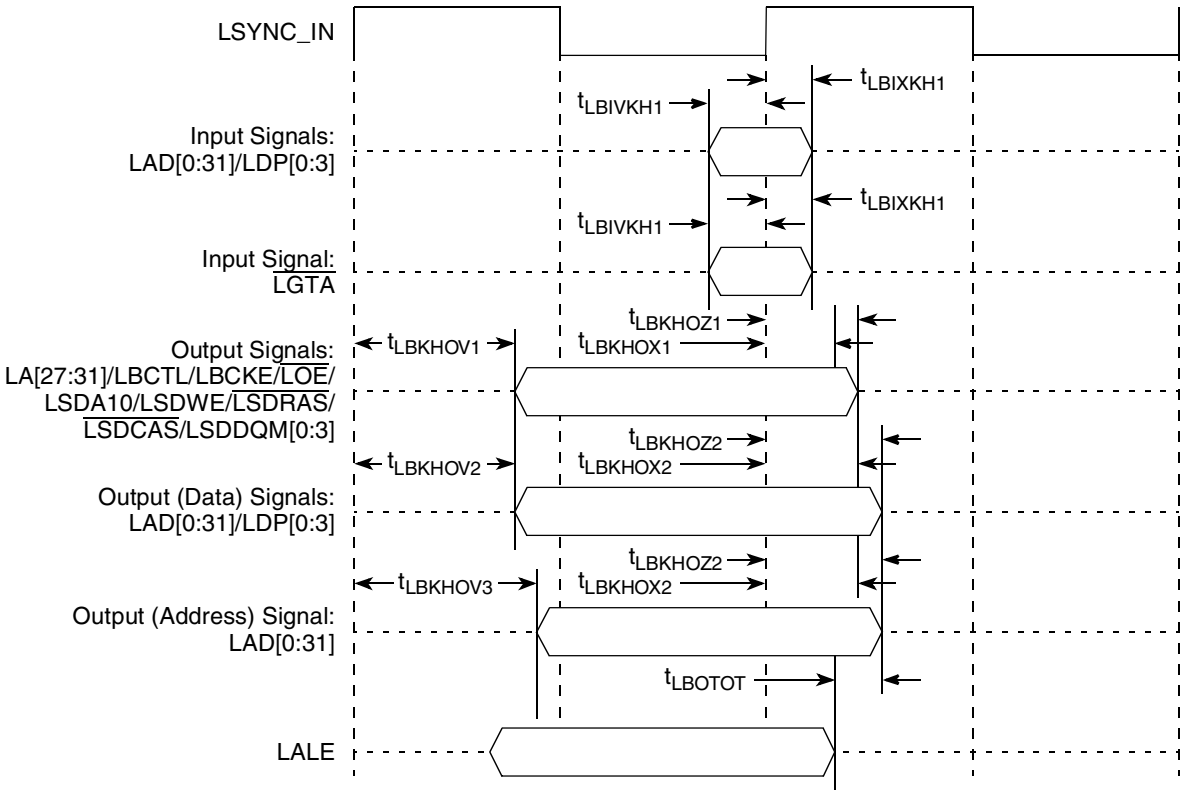


Figure 17. Local Bus Signals, Nonspecial Signals Only (DLL Enabled)

The following two tables are examples of I2C AC parameters at I2C clock value of 100k and 400k respectively.

Table 36. CPM I2C Timing (f_{SCL}=100 kHz)

Characteristic	Expression	Frequency = 100 kHz		Unit
		Min	Max	
SCL clock frequency (slave)	f_{SCL}	—	100	kHz
SCL clock frequency (master)	f_{SCL}	—	100	kHz
Bus free time between transmissions	t_{SDHDL}	4.7	—	µs
Low period of SCL	t_{SCLCH}	4.7	—	µs
High period of SCL	t_{SCHCL}	4	—	µs
Start condition setup time	t_{SCHDL}	2	—	µs
Start condition hold time	t_{SDLCL}	3	—	µs
Data hold time	t_{SCLDX}	2	—	µs
Data setup time	t_{SDVCH}	3	—	µs
SDA/SCL rise time	t_{SRISE}	—	1	µs
SDA/SCL fall time (master)	t_{SFALL}	—	303	ns
Stop condition setup time	t_{SCHDH}	2	—	µs

Table 37. CPM I2C Timing (f_{SCL}=400 kHz)

Characteristic	Expression	Frequency = 400 kHz		Unit
		Min	Max	
SCL clock frequency (slave)	f_{SCL}	—	400	kHz
SCL clock frequency (master)	f_{SCL}	—	400	kHz
Bus free time between transmissions	t_{SDHDL}	1.2	—	µs
Low period of SCL	t_{SCLCH}	1.2	—	µs
High period of SCL	t_{SCHCL}	1	—	µs
Start condition setup time	t_{SCHDL}	420	—	ns
Start condition hold time	t_{SDLCL}	630	—	ns
Data hold time	t_{SCLDX}	420	—	ns
Data setup time	t_{SDVCH}	630	—	ns
SDA/SCL rise time	t_{SRISE}	—	250	ns
SDA/SCL fall time	t_{SFALL}	—	75	ns
Stop condition setup time	t_{SCHDH}	420	—	ns

Figure 39 shows the PCI input AC timing conditions.

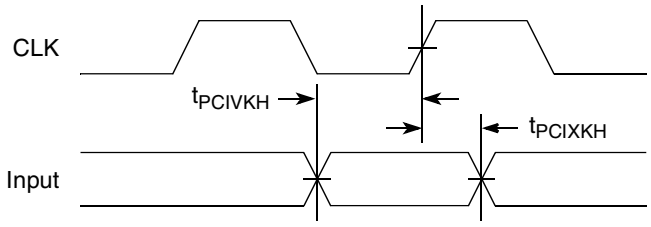


Figure 39. PCI Input AC Timing Measurement Conditions

Figure 40 shows the PCI output AC timing conditions.

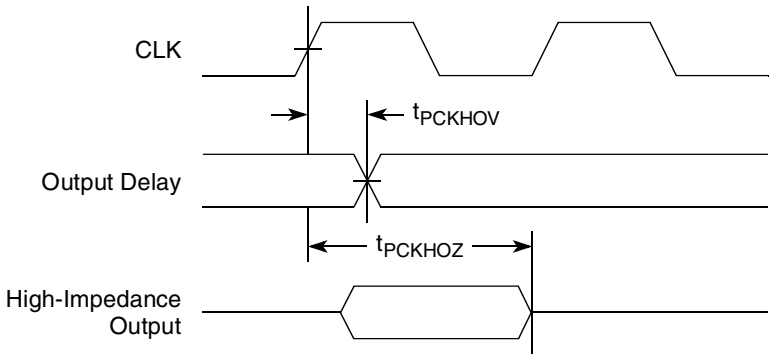


Figure 40. PCI Output AC Timing Measurement Condition

14 Package and Pin Listings

This section details package parameters, pin assignments, and dimensions.

14.1 Package Parameters for the MPC8541E FC-PBGA

The package parameters are as provided in the following list. The package type is 29 mm × 29 mm, 783 flip chip plastic ball grid array (FC-PBGA).

Die size	8.7 mm × 9.3 mm × 0.75 mm
Package outline	29 mm × 29 mm
Interconnects	783
Pitch	1 mm
Minimum module height	3.07 mm
Maximum module height	3.75 mm
Solder Balls	62 Sn/36 Pb/2 Ag
Ball diameter (typical)	0.5 mm

Table 43. MPC8541E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
PCI2_GNT[1:4]	AD18, AE18, AE19, AD19	O	OV_{DD}	5, 9
PCI2_IDSEL	AC22	I	OV_{DD}	—
PCI2_IRDY	AD20	I/O	OV_{DD}	2
PCI2_PERR	AC20	I/O	OV_{DD}	2
PCI2_REQ[0]	AD21	I/O	OV_{DD}	—
PCI2_REQ[1:4]	AE21, AD22, AE22, AC23	I	OV_{DD}	—
PCI2_SERR	AE20	I/O	OV_{DD}	2,4
PCI2_STOP	AC21	I/O	OV_{DD}	2
PCI2_TRDY	AC19	I/O	OV_{DD}	2
DDR SDRAM Memory Interface				
MDQ[0:63]	M26, L27, L22, K24, M24, M23, K27, K26, K22, J28, F26, E27, J26, J23, H26, G26, C26, E25, C24, E23, D26, C25, A24, D23, B23, F22, J21, G21, G22, D22, H21, E21, N18, J18, D18, L17, M18, L18, C18, A18, K17, K16, C16, B16, G17, L16, A16, L15, G15, E15, C14, K13, C15, D15, E14, D14, D13, E13, D12, A11, F13, H13, A13, B12	I/O	GV_{DD}	—
MECC[0:7]	N20, M20, L19, E19, C21, A21, G19, A19	I/O	GV_{DD}	—
MDM[0:8]	L24, H28, F24, L21, E18, E16, G14, B13, M19	O	GV_{DD}	—
MDQS[0:8]	L26, J25, D25, A22, H18, F16, F14, C13, C20	I/O	GV_{DD}	—
MBA[0:1]	B18, B19	O	GV_{DD}	—
MA[0:14]	N19, B21, F21, K21, M21, C23, A23, B24, H23, G24, K19, B25, D27, J14, J13	O	GV_{DD}	—
MWE	D17	O	GV_{DD}	—
MRAS	F17	O	GV_{DD}	—
MCAS	J16	O	GV_{DD}	—
MCS[0:3]	H16, G16, J15, H15	O	GV_{DD}	—
MCKE[0:1]	E26, E28	O	GV_{DD}	11
MCK[0:5]	J20, H25, A15, D20, F28, K14	O	GV_{DD}	—
MCK[0:5]	F20, G27, B15, E20, F27, L14	O	GV_{DD}	—
MSYNC_IN	M28	I	GV_{DD}	22
MSYNC_OUT	N28	O	GV_{DD}	22
Local Bus Controller Interface				
LA[27]	U18	O	OV_{DD}	5, 9

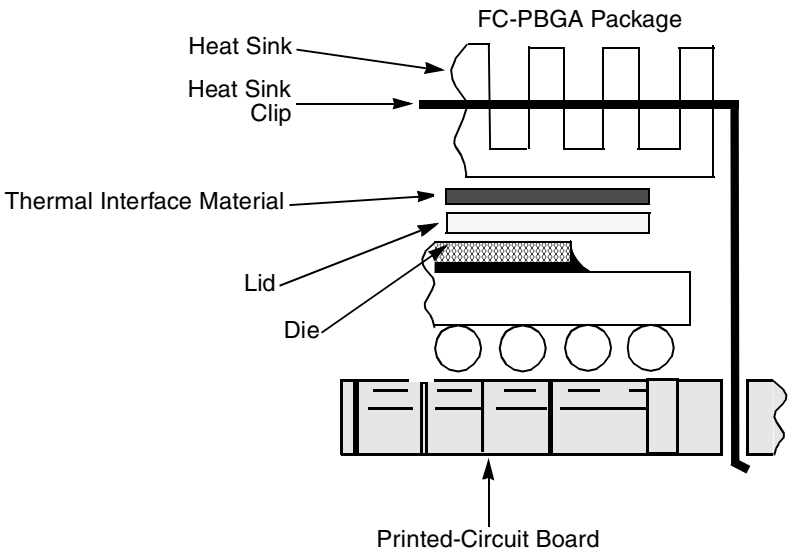


Figure 42. Package Exploded Cross-Sectional View with Several Heat Sink Options

The system board designer can choose between several types of heat sinks to place on the MPC8541E. There are several commercially-available heat sinks from the following vendors:

Aavid Thermalloy 80 Commercial St. Concord, NH 03301 Internet: www.aavidthermalloy.com	603-224-9988
Alpha Novatech 473 Sapena Ct. #15 Santa Clara, CA 95054 Internet: www.alphanovatech.com	408-749-7601
International Electronic Research Corporation (IERC) 413 North Moss St. Burbank, CA 91502 Internet: www.ctscorp.com	818-842-7277
Millennium Electronics (MEI) Loroco Sites 671 East Brokaw Road San Jose, CA 95112 Internet: www.mei-millennium.com	408-436-8770
Tyco Electronics Chip Coolers™ P.O. Box 3668 Harrisburg, PA 17105-3668 Internet: www.chipcoolers.com	800-522-6752
Wakefield Engineering 33 Bridge St. Pelham, NH 03076 Internet: www.wakefield.com	603-635-5102

17 System Design Information

This section provides electrical and thermal design recommendations for successful application of the MPC8541E.

17.1 System Clocking

The MPC8541E includes five PLLs.

1. The platform PLL ($AV_{DD}1$) generates the platform clock from the externally supplied SYSCLK input. The frequency ratio between the platform and SYSCLK is selected using the platform PLL ratio configuration bits as described in Section 15.2, "Platform/System PLL Ratio."
2. The e500 Core PLL ($AV_{DD}2$) generates the core clock as a slave to the platform clock. The frequency ratio between the e500 core clock and the platform clock is selected using the e500 PLL ratio configuration bits as described in Section 15.3, "e500 Core PLL Ratio."
3. The CPM PLL ($AV_{DD}3$) is slaved to the platform clock and is used to generate clocks used internally by the CPM block. The ratio between the CPM PLL and the platform clock is fixed and not under user control.
4. The PCI1 PLL ($AV_{DD}4$) generates the clocking for the first PCI bus.
5. The PCI2 PLL ($AV_{DD}5$) generates the clock for the second PCI bus.

17.2 PLL Power Supply Filtering

Each of the PLLs listed above is provided with power through independent power supply pins ($AV_{DD}1$, $AV_{DD}2$, $AV_{DD}3$, $AV_{DD}4$, and $AV_{DD}5$ respectively). The AV_{DD} level should always be equivalent to V_{DD}, and preferably these voltages are derived directly from V_{DD} through a low frequency filter scheme such as the following.

There are a number of ways to reliably provide power to the PLLs, but the recommended solution is to provide five independent filter circuits as illustrated in Figure 49, one to each of the five AV_{DD} pins. By providing independent filters to each PLL the opportunity to cause noise injection from one PLL to the other is reduced.

This circuit is intended to filter noise in the PLLs resonant frequency range from a 500 kHz to 10 MHz range. It should be built with surface mount capacitors with minimum Effective Series Inductance (ESL). Consistent with the recommendations of Dr. Howard Johnson in *High Speed Digital Design: A Handbook of Black Magic* (Prentice Hall, 1993), multiple small capacitors of equal value are recommended over a single large value capacitor.

Each circuit should be placed as close as possible to the specific AV_{DD} pin being supplied to minimize noise coupled from nearby circuits. It should be possible to route directly from the capacitors to the AV_{DD} pin, which is on the periphery of the 783 FC-PBGA footprint, without the inductance of vias.

Figure 49 shows the PLL power supply filter circuit.

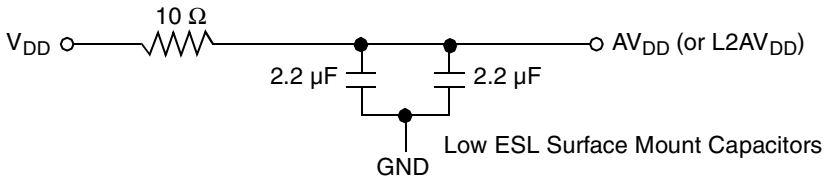


Figure 49. PLL Power Supply Filter Circuit

17.3 Decoupling Recommendations

Due to large address and data buses, and high operating frequencies, the MPC8541E can generate transient power surges and high frequency noise in its power supply, especially while driving large capacitive loads. This noise must be prevented from reaching other components in the MPC8541E system, and the MPC8541E itself requires a clean, tightly regulated source of power. Therefore, it is recommended that the system designer place at least one decoupling capacitor at each V_{DD}, OV_{DD}, GV_{DD}, and LV_{DD} pins of the MPC8541E. These decoupling capacitors should receive their power from separate V_{DD}, OV_{DD}, GV_{DD}, LV_{DD}, and GND power planes in the PCB, utilizing short traces to minimize inductance. Capacitors may be placed directly under the device using a standard escape pattern. Others may surround the part.

These capacitors should have a value of 0.01 or 0.1 µF. Only ceramic SMT (surface mount technology) capacitors should be used to minimize lead inductance, preferably 0402 or 0603 sizes.

In addition, it is recommended that there be several bulk storage capacitors distributed around the PCB, feeding the V_{DD}, OV_{DD}, GV_{DD}, and LV_{DD} planes, to enable quick recharging of the smaller chip capacitors. These bulk capacitors should have a low ESR (equivalent series resistance) rating to ensure the quick response time necessary. They should also be connected to the power and ground planes through two vias to minimize inductance. Suggested bulk capacitors—100–330 µF (AVX TPS tantalum or Sanyo OSCON).

17.4 Connection Recommendations

To ensure reliable operation, it is highly recommended to connect unused inputs to an appropriate signal level. Unused active low inputs should be tied to OV_{DD}, GV_{DD}, or LV_{DD} as required. Unused active high inputs should be connected to GND. All NC (no-connect) signals must remain unconnected.

Power and ground connections must be made to all external V_{DD}, GV_{DD}, LV_{DD}, OV_{DD}, and GND pins of the MPC8541E.

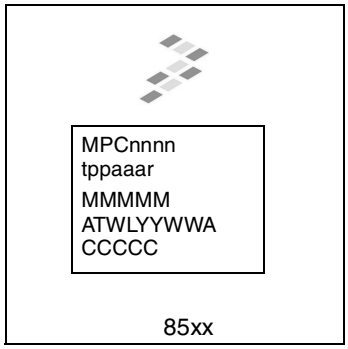
17.5 Output Buffer DC Impedance

The MPC8541E drivers are characterized over process, voltage, and temperature. For all buses, the driver is a push-pull single-ended driver type (open drain for I^2C).

To measure Z_0 for the single-ended drivers, an external resistor is connected from the chip pad to OV_{DD} or GND. Then, the value of each resistor is varied until the pad voltage is $OV_{DD}/2$ (see Figure 50). The output impedance is the average of two components, the resistances of the pull-up and pull-down devices.

19.2 Part Marking

Parts are marked as the example shown in Figure 53.



FC-PBGA

Notes:

MMMMM is the 5-digit mask number.
ATWLYYWWA is the traceability code.
CCCCC is the country of assembly. This space is left blank if parts are assembled in the United States.

Figure 53. Part Marking for FC-PBGA Device

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